

TOSHIBA TRANSISTOR SILICON PNP TRIPLE DIFFUSED TYPE (DARLINGTON POWER)

2SB1020A

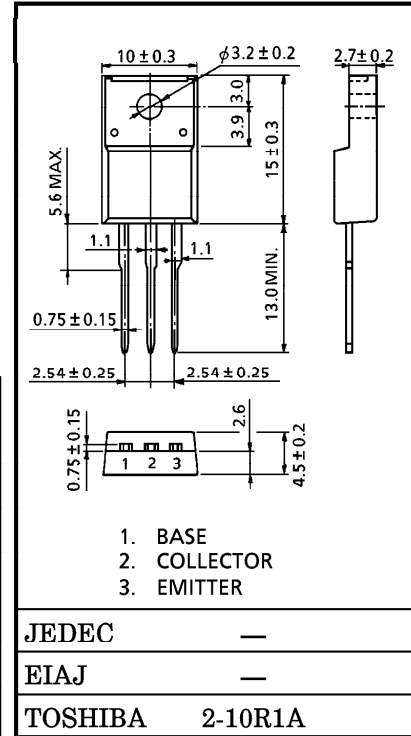
HIGH POWER SWITCHING APPLICATIONS

HAMMER DRIVE, PULSE MOTOR DRIVE APPLICATIONS

- High DC Current Gain
: $h_{FE} = 2000$ (Min.) (at $V_{CE} = -3V$, $I_C = -3A$)
- Low Saturation Voltage
: $V_{CE(sat)} = -1.5V$ (Max.) (at $I_C = -3A$)
- Complementary to 2SD1415A

INDUSTRIAL APPLICATIONS

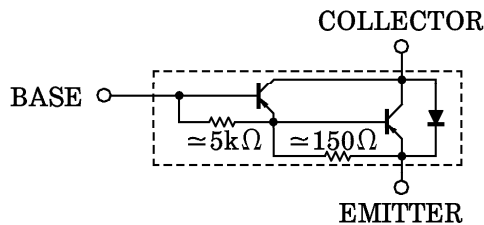
Unit in mm



MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	-100	V
Collector-Emitter Voltage		V_{CEO}	-100	V
Emitter-Base Voltage		V_{EBO}	-5	V
Collector Current	DC	I_C	-7	A
	Pulse	I_{CP}	-10	
Base Current		I_B	-0.7	A
Collector Power Dissipation		P_C	2.0	W
			30	
Junction Temperature		T_j	150	$^\circ C$
Storage Temperature Range		T_{stg}	-55~150	$^\circ C$

EQUIVALENT CIRCUIT



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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	$V_{CB} = -100V, I_E = 0$	—	—	-100	μA
Emitter Cut-off Current		I_{EBO}	$V_{EB} = -5V, I_C = 0$	—	—	-4.0	mA
Collector-Emitter Breakdown Voltage		$V_{(BR)CEO}$	$I_C = -50mA, I_B = 0$	-100	—	—	V
DC Current Gain		$h_{FE(1)}$	$V_{CE} = -3V, I_C = -3A$	2000	—	15000	
		$h_{FE(2)}$	$V_{CE} = -3V, I_C = -7A$	1000	—	—	
Collector-Emitter Saturation Voltage		$V_{CE(sat)(1)}$	$I_C = -3A, I_B = -6mA$	—	-0.95	-1.5	V
		$V_{CE(sat)(2)}$	$I_C = -7A, I_B = -14mA$	—	-1.3	-2.0	
Base-Emitter Saturation Voltage		$V_{BE(sat)}$	$I_C = -3A, I_B = -6mA$	—	-1.55	-2.5	V
Switching Time	Turn-on Time	t_{on}	<p> $-I_{B1} = I_{B2} = 6mA,$ $DUTY\ CYCLE \leq 1\%$ </p>	—	0.8	—	μs
	Storage Time	t_{stg}		—	2.0	—	
	Fall Time	t_f		—	—	2.5	

